# **General Purpose Transistor**

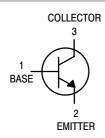
# **NPN Silicon**

### **Features**

• Pb-Free Package is Available



## http://onsemi.com





SOT-23 CASE 318 STYLE 6

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	$V_{CEO}$	32	Vdc
Collector - Base Voltage	$V_{CBO}$	60	Vdc
Emitter – Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	800	mAdc

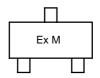
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1), T <sub>A</sub> = 25°C	P <sub>D</sub>	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	556	°C/W
Total Device Dissipation Alumina	P <sub>D</sub>	200	\//
Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C		300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in 99.5% alumina.

## **MARKING DIAGRAM**



EA = Specific Device Code (BCW65ALT1) EC = Specific Device Code (BCW65CLT1)

M = Date Code

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BCW65ALT1	SOT-23	3000 / Tape & Reel
BCW65ALT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BCW65CLT1	SOT-23	3000 / Tape & Reel

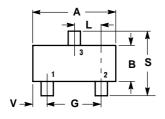
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

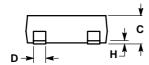
# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

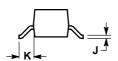
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			<u></u>	<u>.</u>	
Collector – Emitter Breakdown Voltage $(I_C = 10 \text{ mAdc}, I_B = 0)$	V <sub>(BR)CEO</sub>	32	_	-	Vdc
Collector – Emitter Breakdown Voltage ( $I_C = 10 \mu Adc$ , $V_{EB} = 0$ )	V <sub>(BR)CES</sub>	60	-	-	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	5.0	-	-	Vdc
Collector Cutoff Current $(V_{CE} = 32 \text{ Vdc}, I_E = 0)$ $(V_{CE} = 32 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$	I <sub>CES</sub>	-	_ _	20 20	nAdc μAdc
Emitter Cutoff Current $(V_{EB} = 4.0 \text{ Vdc}, I_C = 0)$	I <sub>EBO</sub>	-	_	20	nAdc
ON CHARACTERISTICS					
DC Current Gain BCW65ALT1 $ \begin{aligned} &(I_C = 100 \ \mu\text{Adc}, \ V_{CE} = 10 \ \text{Vdc}) \\ &(I_C = 10 \ \text{mAdc}, \ V_{CE} = 1.0 \ \text{Vdc}) \\ &(I_C = 100 \ \text{mAdc}, \ V_{CE} = 1.0 \ \text{Vdc}) \\ &(I_C = 500 \ \text{mAdc}, \ V_{CE} = 2.0 \ \text{Vdc}) \end{aligned} $	h <sub>FE</sub>	35 75 100 35	- - - -	- - 250 -	-
DC Current Gain BCW65CLT1 ( $I_C = 100  \mu Adc,  V_{CE} = 10  Vdc$ ) ( $I_C = 10  m Adc,  V_{CE} = 1.0  Vdc$ ) ( $I_C = 100  m Adc,  V_{CE} = 1.0  Vdc$ ) ( $I_C = 500  m Adc,  V_{CE} = 2.0  Vdc$ )	om.c	80 180 250 100	- - - -	- - 630 -	-
Collector – Emitter Saturation Voltage ( $I_C = 500 \text{ mAdc}$ , $I_B = 50 \text{ mAdc}$ ) ( $I_C = 100 \text{ mAdc}$ , $I_B = 10 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	-	0.7 0.3	- -	Vdc
Base – Emitter Saturation Voltage (I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc)	V <sub>BE(sat)</sub>	ı	_	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain — Bandwidth Product ( $I_C = 20 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 100 \text{ MHz}$ )	f <sub>T</sub>	100	-	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	-	12	pF
Input Capacitance ( $V_{EB} = 0.5 \text{ Vdc}$ , $I_{C} = 0$ , $f = 1.0 \text{ MHz}$ )	C <sub>ibo</sub>	-	-	80	pF
Noise Figure ( $V_{CE}$ = 5.0 Vdc, $I_{C}$ = 0.2 mAdc, $R_{S}$ = 1.0 k $\Omega$ , f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB
SWITCHING CHARACTERISTICS					
Turn–On Time $(I_{B1} = I_{B2} = 15 \text{ mAdc})$	t <sub>on</sub>	-	_	100	ns
Turn–Off Time (I <sub>C</sub> = 150 mAdc, R <sub>L</sub> = 150 $\Omega$ )	t <sub>off</sub>	-	_	400	ns

## **PACKAGE DIMENSIONS**

SOT-23 (TO-236) CASE 318-08 **ISSUE AK** 





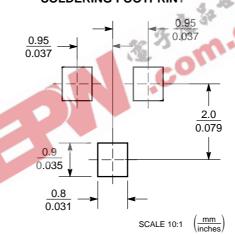


BASE EMITTER COLLECTOR

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.1102	0.1197	2.80	3.04	
В	0.0472	0.0551	1.20	1.40	
С	0.0350	0.0440	0.89	1.11	
D	0.0150	0.0200	0.37	0.50	
G	0.0701	0.0807	1.78	2.04	
Н	0.0005	0.0040	0.013	0.100	
J	0.0034	0.0070	0.085	0.177	
K	0.0140	0.0285	0.35	0.69	
L	0.0350	0.0401	0.89	1.02	
S	0.0830	0.1039	2.10	2.64	
V	0.0177	0.0236	0.45	0.60	

# **SOLDERING FOOTPRINT**



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SCALE 10:1



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